



Silicon Carbide PiN Diode ASCPDA00210KF

V_{RRM}	=	10 kV
I_F	=	2 A
V_F	=	3.8 V

Features

- 10kV blocking
- 3DSiC® technology
- Lowest on-state voltage
- Epitaxial emitter

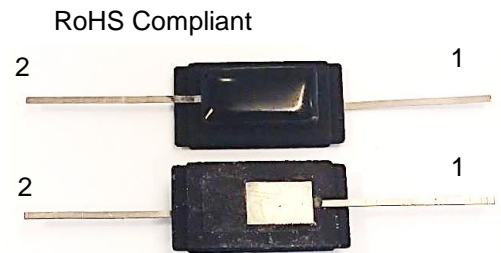
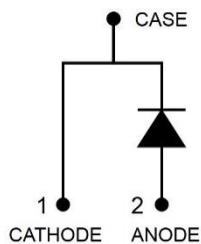
Applications

- General purpose
- Voltage multiplier
- Electrostatic systems
- X-Ray systems

Advantages

- Reduced stacking
- Fast switching
- Low reverse recovery
- Low losses
- Avalanche capability

Package



Absolute Maximum Ratings

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	Peak repetitive Reverse Voltage		10	kV
I_F	Continuous Forward Current	$T_C = 25^\circ\text{C}$ $T_C = 150^\circ\text{C}$	2	A
$I_{F,Max}$	Non-repetitive Peak Forward Current	$T_C = 25^\circ\text{C}$, $t_p = 10\mu\text{s}$, pulse $T_C = 150^\circ\text{C}$, $t_p = 10\mu\text{s}$, pulse		A
I_{FSM}	Non-repetitive Forward Surge Current	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$, half sine pulse $T_C = 150^\circ\text{C}$, $t_p = 10\text{ms}$, half sine pulse		A
P_{tot}	Power Dissipation	$T_C = 25^\circ\text{C}$ $T_C = 150^\circ\text{C}$		W
T_J	Operating Junction Temperature Range		-55 to +175	$^\circ\text{C}$

Electrical Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F = 2\text{ A}$, $T_C = 25^\circ\text{C}$ $I_F = 2\text{ A}$, $T_C = 125^\circ\text{C}$ $I_F = 2\text{ A}$, $T_C = 175^\circ\text{C}$		3.8 3.6 3.45		V
V_{BR}	Breakdown voltage	$T_C = 25^\circ\text{C}$	11	13.5	14.5	kV
I_R	Reverse Current	$V_R = 10\text{ kV}$, $T_C = 25^\circ\text{C}$			10	nA
Q_{rr}	Reverse Recovery Charge	$I_F = 2\text{ A}$, $V_R = 200\text{ V}$, $di/dt = 20\text{ A}/\mu\text{s}$, $T_C = 25^\circ\text{C}$		62		nC
t_{rr}	Reverse recovery time	$I_F = 2\text{ A}$, $di/dt = 20\text{ A}/\mu\text{s}$		158		ns
C	Total Capacitance	$V_R = 1\text{ V}$, $f = 200\text{ kHz}$ $V_R = 10\text{ V}$, $f = 200\text{ kHz}$ $V_R = 200\text{ V}$, $f = 200\text{ kHz}$		52 29 8		pF

Thermal Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case				$^\circ\text{C}/\text{W}$

Typical Performance

Fig. 1. Forward Characteristics

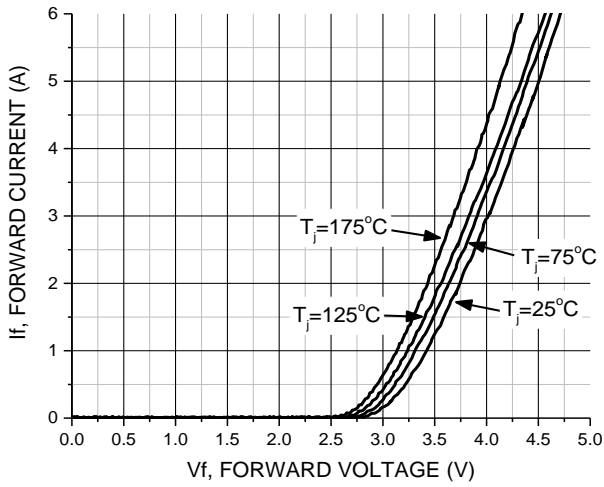


Fig. 2. Reverse Characteristics at 25°C

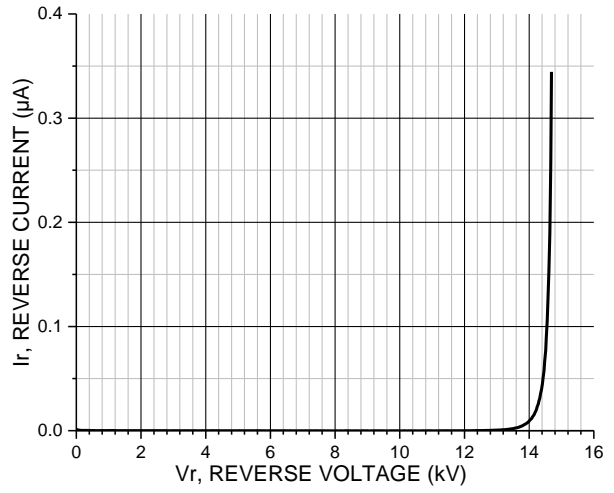


Fig. 3. Typical Turn Off Characteristics

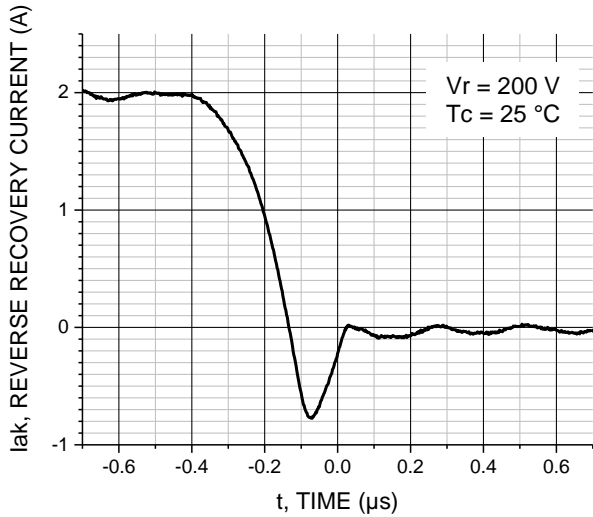


Fig. 4. Reverse Recovery Charge vs. Current

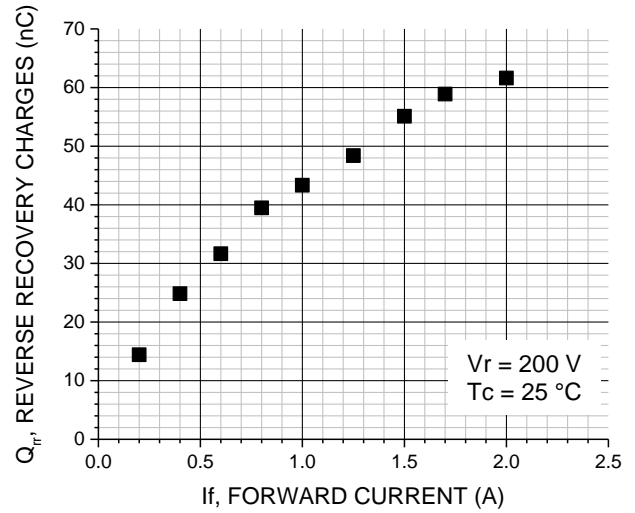
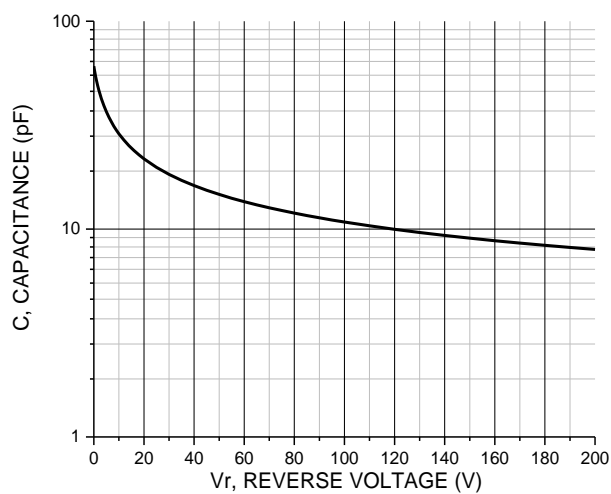
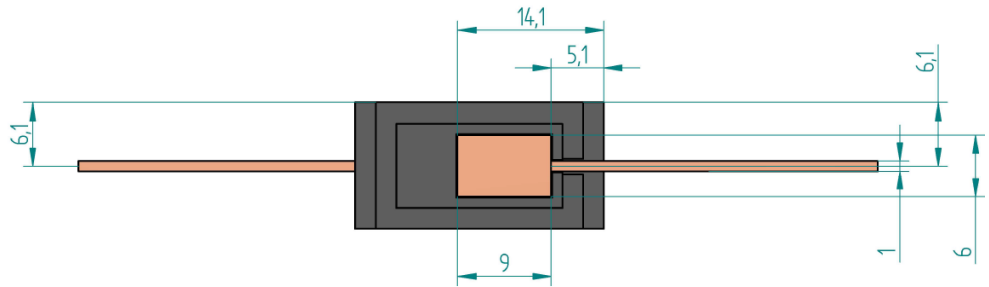
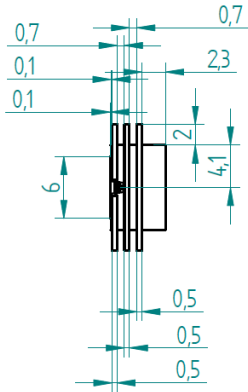
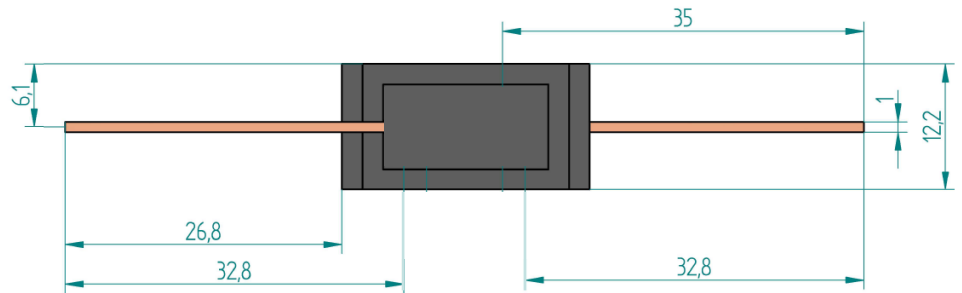
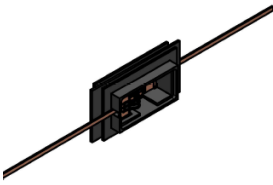


Fig. 5. Capacitance vs. Reverse Voltage



Package Dimensions



Dimensions in millimeters

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Information

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